

Artur Tuktamyshev

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/4480275/publications.pdf>

Version: 2024-02-01

22
papers

147
citations

1307366

7
h-index

1199470

12
g-index

22
all docs

22
docs citations

22
times ranked

142
citing authors

#	ARTICLE	IF	CITATIONS
1	High-temperature droplet epitaxy of symmetric GaAs/AlGaAs quantum dots. <i>Scientific Reports</i> , 2020, 10, 6532.	1.6	22
2	Pseudomorphic GeSiSn, SiSn and Ge layers in strained heterostructures. <i>Nanotechnology</i> , 2018, 29, 154002.	1.3	19
3	Splitting of frequencies of optical phonons in tensile-strained germanium layers. <i>JETP Letters</i> , 2017, 105, 327-331.	0.4	15
4	Morphology, Structure, and Optical Properties of Semiconductor Films with GeSiSn Nanoislands and Strained Layers. <i>Nanoscale Research Letters</i> , 2018, 13, 29.	3.1	15
5	Spectral broadening in self-assembled GaAs quantum dots with narrow size distribution. <i>Journal of Applied Physics</i> , 2019, 126, .	1.1	13
6	Telecom-wavelength InAs QDs with low fine structure splitting grown by droplet epitaxy on GaAs(111)A vicinal substrates. <i>Applied Physics Letters</i> , 2021, 118, .	1.5	12
7	Temperature Activated Dimensionality Crossover in the Nucleation of Quantum Dots by Droplet Epitaxy on GaAs(111)A Vicinal Substrates. <i>Scientific Reports</i> , 2019, 9, 14520.	1.6	11
8	Nucleation of Ga droplets self-assembly on GaAs(111)A substrates. <i>Scientific Reports</i> , 2021, 11, 6833.	1.6	6
9	Controlling the threshold voltage of a semiconductor field-effect transistor by gating its graphene gate. <i>Npj 2D Materials and Applications</i> , 2022, 6, .	3.9	6
10	Strained multilayer structures with pseudomorphic GeSiSn layers. <i>Semiconductors</i> , 2016, 50, 1584-1588.	0.2	5
11	Self-assembled strained GeSiSn nanoscale structures grown by MBE on Si(100). <i>Journal of Crystal Growth</i> , 2017, 457, 215-219.	0.7	5
12	Growth of Epitaxial SiSn Films with High Sn Content for IR Converters. <i>Russian Physics Journal</i> , 2017, 60, 354-359.	0.2	5
13	Initial growth stages of Si-Ge-Sn ternary alloys grown on Si (100) by low-temperature molecular-beam epitaxy. <i>Semiconductors</i> , 2015, 49, 1582-1586.	0.2	3
14	Sn influence on MBE growth of GeSiSn/Si MQW. <i>Journal of Physics: Conference Series</i> , 2017, 816, 012020.	0.3	3
15	Valence-band offsets in strained SiGeSn/Si layers with different tin contents. <i>Semiconductors</i> , 2017, 51, 329-334.	0.2	2
16	Reentrant Behavior of the Density vs. Temperature of Indium Islands on GaAs(111)A. <i>Nanomaterials</i> , 2020, 10, 1512.	1.9	2
17	Optically controlled dual-band quantum dot infrared photodetector. <i>Nanomaterials and Nanotechnology</i> , 2022, 12, 184798042210857.	1.2	2
18	Effect of a Stepped Si(100) Surface on the Nucleation Process of Ge Islands. <i>Russian Physics Journal</i> , 2018, 60, 1864-1870.	0.2	1

#	ARTICLE	IF	CITATIONS
19	Synthesis of Epitaxial Films Based on Ge-Sn Materials with Ge/GeSn, Ge/GeSiSn, and GeSn/GeSiSn Heterojunctions. Russian Physics Journal, 2015, 58, 965-969.	0.2	0
20	The ordering of Ge islands on a stepped Si(100) surface. Journal of Physics: Conference Series, 2017, 816, 012015.	0.3	0
21	Elastically strained GeSiSn layers and GeSiSn islands in multilayered periodical structures. Modern Electronic Materials, 2017, 3, 86-90.	0.2	0
22	Formation of a Stepped Si(100) Surface and Its Effect on the Growth of Ge Islands. Semiconductors, 2018, 52, 390-393.	0.2	0